

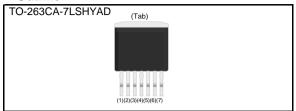
N-channel SiC power MOSFET

V_{DSS}	1700V
R _{DS(on)} (Typ.)	1.15Ω
I _D	3.9A
P_D	39W

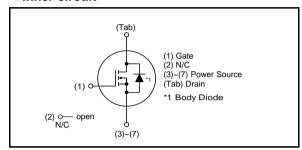
● Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Wide creepage distance = 6.1 mm
- 4) Simple to drive
- 5) Pb-free lead plating; RoHS compliant

●Outline



•Inner circuit



Application

- · Auxilialy power supplies
- ·Switch mode power supplies

Packaging specifications

	J J - P	
	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Type	Basic ordering unit (pcs)	800
	Taping code	TL1
	Marking	SCT2H12NWB

● **Absolute maximum ratings** (T_{vj} = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain - Source voltage			V_{DSS}	1700	V
Continuous drain	$V_{GS} = V_{GS \text{ on}}$	T _c = 25°C	*1	3.9	А
and source current	VGS - VGS_on	T _c = 100°C	I _D , I _S *1	2.8	А
Pulsed drain current	$V_{GS} = V_{GS_on}$	T _c = 25°C	I _{D,pulse} *1	5.6	А
Body diode pulsed forward current $T_c = 25^{\circ}\text{C}$ $V_{GS} = 0 \text{ V}$			I _{S,pulse} *1	5.6	А
Gate - Source voltage (DC)			V_{GSS_DC}	-6 to 22	V
Gate - Source surge voltage (t _{surge} <300ns)			V _{GSS_surge} *2	-10 to 26	V
Power dissipation (T _c = 25°C)			P_D	39	W
Virtual Junction temperature			T_{vj}	175	°C
Range of storage temperature			T_{stg}	-55 to +175	°C

●Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Cumb of	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	$V_{(BR)DSS}$ $V_{GS} = 0V$, $I_D = 1mA$		1700	-	-	V	
		$V_{DS} = 1700V, V_{GS} = 0V$					
Zero gate voltage drain current	I _{DSS}	$T_{vj} = 25$ °C	-	0.1	10	μΑ	
		T _{vj} = 150°C	-	0.2	-		
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}, I_D = 0.41 \text{mA}$	1.6	2.8	4.0	V	

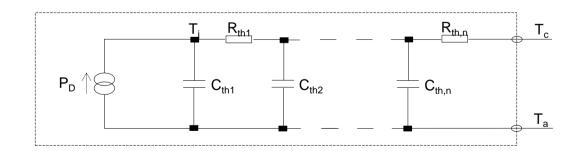
●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC}	-	2.94	3.83	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit		
R _{th1}	5.9 × 10 ⁻¹			
R _{th2}	1.3×10^{-0}	K/W		
R _{th3}	1.1 × 10 °			

Symbol	Value	Unit
C _{th1}	1.4 × 10 ⁻³	
C _{th2}	8.8 × 10 ⁻²	Ws/K
C _{th3}	3.5 × 10 ⁻³	



ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	UTIIL	
		$V_{GS} = 18V, I_D = 1.1A$					
Static drain - source on - state resistance	R _{DS(on)} *3	T _{vj} = 25°C	-	1.15	1.50	Ω	
		T _{vj} = 125°C	-	1.71	-		
Gate input resistance	R_{G}	f = 1MHz, open drain	-	49	-	Ω	
Transconductance	g fs *3	$V_{DS} = 10V, I_D = 1.1A$	-	0.4	-	S	
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	197	-		
Output capacitance	C _{oss}	V _{DS} = 800V	-	8	-	pF	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	2	-		
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	11	-	pF	
Total gate charge	Q_g^{*3}	$V_{DD} = 800V$	-	24	-		
Gate - Source charge	Q _{gs} *3	I _D = 2A	-	8	-	nC	
Gate - Drain charge	Q _{gd} *3	V _{GS} = 18V	-	5	-		
Gate plateau voltage	V _(plateau)	$V_{DD} = 800V, I_D = 2A$	1	7.4	-	V	
Turn - on delay time	t _{d(on)} *3		-	12	-		
Rise time	t _r *3		-	25	-	20	
Turn - off delay time	t _{d(off)} *3	$V_{DD} = 800V, I_{D} = 2A$ $V_{GS} = 18V/0V$	-	24	-	ns	
Fall time	t _f *3	$R_G = 0Ω$, L=250 μ H	-	32	-		
Turn - on switching loss	E _{on} *3	*E _{on} includes diode	-	81	-		
Turn - off switching loss	E _{off} *3	reverse recovery	-	2	-	μJ	

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

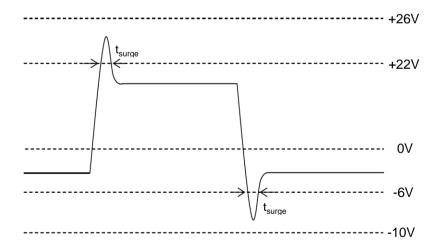
Parameter	Symbol	Conditions	Values			Unit
raiametei	Symbol Conditions -		Min.	Тур.	Max.	Offic
Forward voltage	V _{SD} *3	$V_{GS} = 0V, I_{S} = 1.1A$	-	4.3	-	V
Reverse recovery time	t _{rr} *3		-	39	-	ns
Reverse recovery charge	Q _{rr} *3	$I_F = 1.1A, V_R = 800V$ di/dt = 650A/µs	-	34	-	nC
Peak reverse recovery current	I _{rrm} *3		-	1.8	-	Α

●Electrostatic Discharge^{*4}

Test	Reference Standard	Conditions	Classification Levels
Human Body Model (HBM)	ANSI/ESDA/JEDEC JS-001-2023	C=100pF, R=1.5kΩ	1A [*] (< 500V)
Charged Device Model (CDM)	ANSI/ESDA/JEDEC JS-002-2022	-	C3 [*] (≧1kV)

^{*} Noted: This is reference data from a random sampling test under conditions confirming to the above standards. ROHM does not guarantee classification Level of Electrostatic Discharge.

^{*2} Example of acceptable V_{GS} waveform



^{*3} Pulsed

^{*1} Limited by maximum T_{vi} and for Max. R_{thJC}.

^{*4} This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

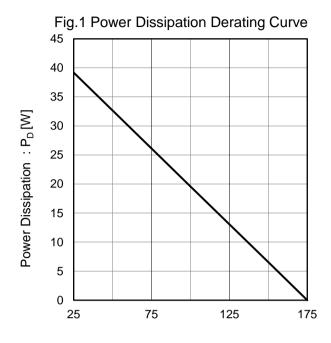
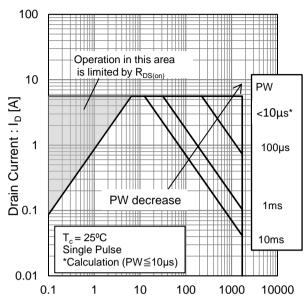
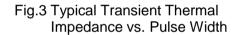


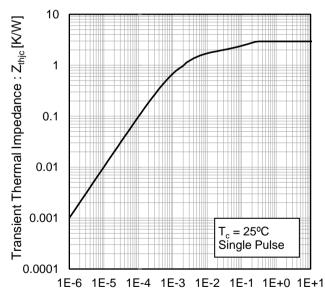
Fig.2 Maximum Safe Operating Area



Case Temperature : T_c [°C]

Drain - Source Voltage : V_{DS} [V]





Pulse Width: PW [s]

Fig.4 Typical Output Characteristics

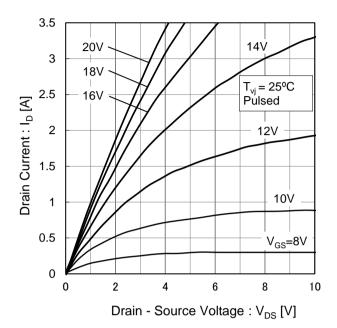
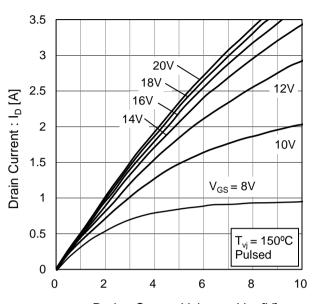
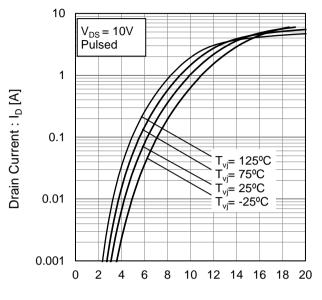


Fig.5 T_{vj} = 150°C Typical Output Characteristics



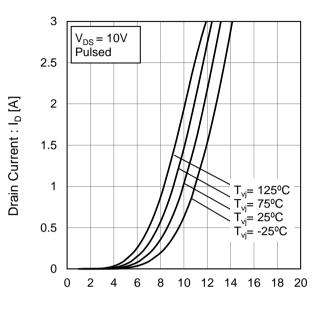
Drain - Source Voltage : V_{DS} [V]

Fig.6 Typical Transfer Characteristics (I)



Gate - Source Voltage : V_{GS} [V]

Fig.7 Typical Transfer Characteristics (II)



Gate - Source Voltage : V_{GS} [V]

Fig.8 Gate Threshold Voltage vs. Virtual Junction Temperature

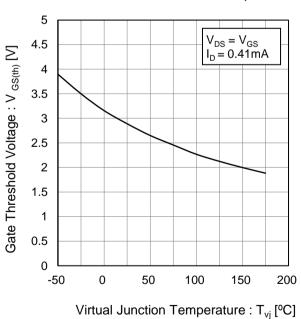


Fig.9 Transconductance vs. Drain Current

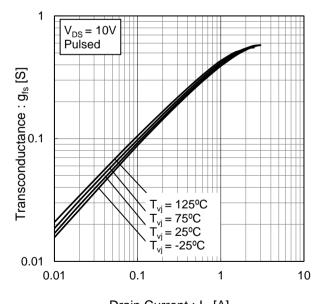


Fig.10 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

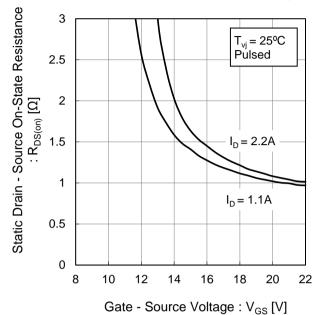


Fig.11 Static Drain - Source On - State Resistance vs. Virtual Junction Temperature

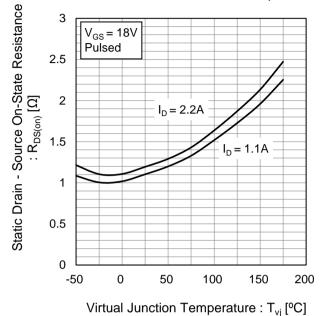
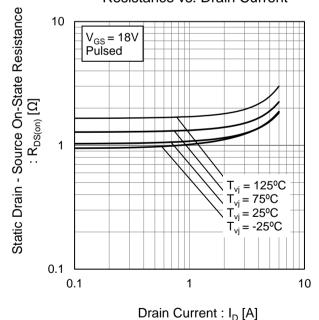


Fig.12 Static Drain - Source On - State Resistance vs. Drain Current



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Fig.13 Typical Capacitance vs. Drain - Source Voltage

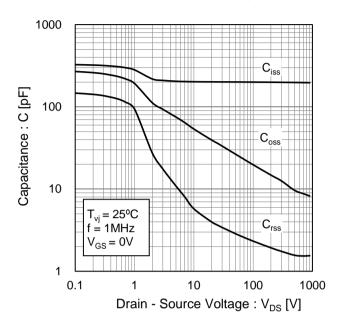


Fig.14 Coss Stored Energy

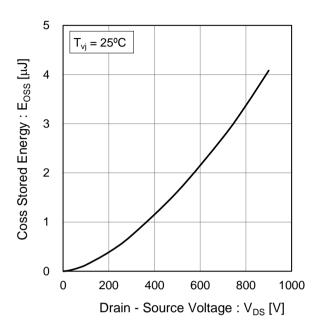


Fig.15 Switching Characteristics

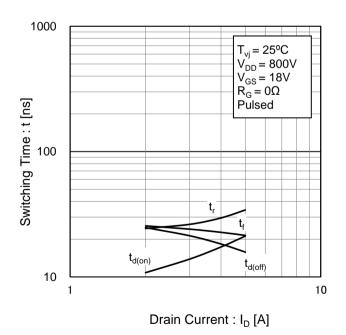


Fig.16 Dynamic Input Characteristics

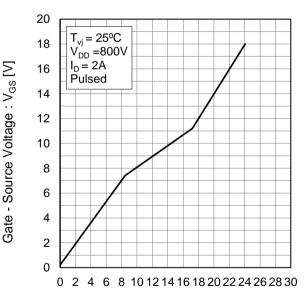


Fig.17 Typical Switching Loss vs. Drain - Source Voltage

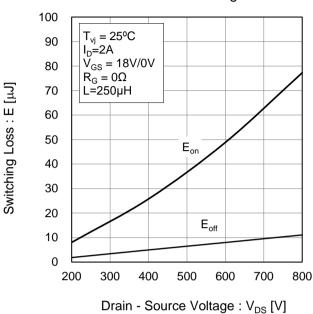
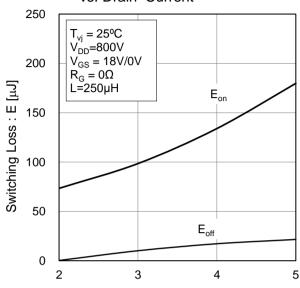


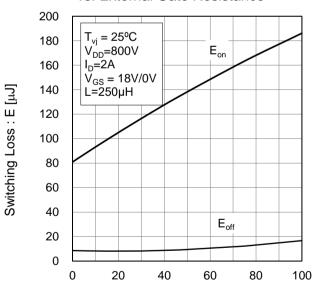
Fig.18 Typical Switching Loss vs. Drain Current

Datasheet



Drain - Current : I_D [A]

Fig.19 Typical Switching Loss vs. External Gate Resistance



External Gate Resistance : $R_G[\Omega]$

Fig.20 Inverse Diode Forward Current vs. Source - Drain Voltage

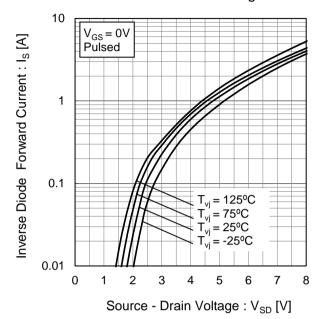
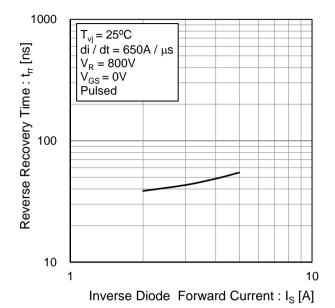


Fig.21 Reverse Recovery Time vs.Inverse Diode Forward Current



Measurement circuits

Fig.1-1 Gate Charge Measurement Circuit

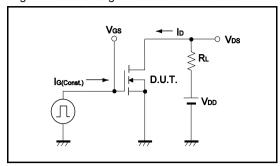


Fig.2-1 Switching Characteristics Measurement Circuit

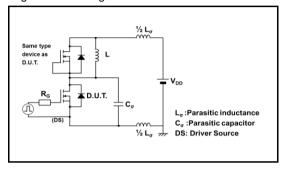


Fig.2-3 Waveforms for Switching Energy Loss

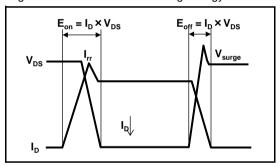


Fig.3-1 Reverse Recovery Time Measurement Circuit

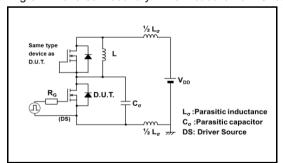


Fig.1-2 Gate Charge Waveform

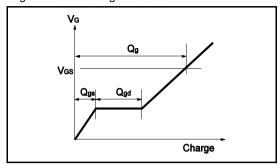


Fig.2-2 Waveforms for Switching Time

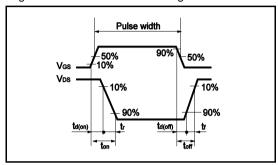
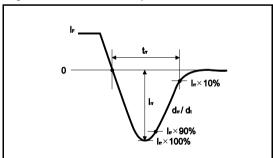
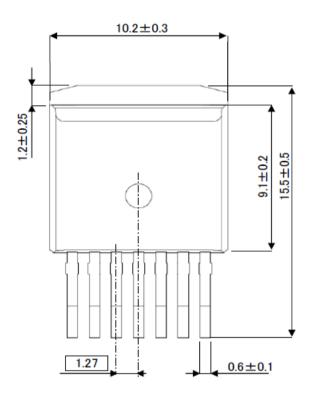


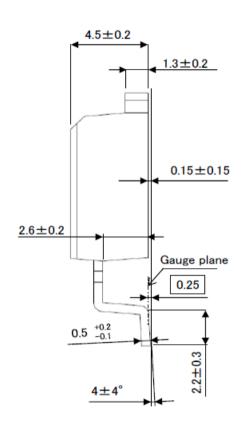
Fig.3-2 Reverse Recovery Waveform

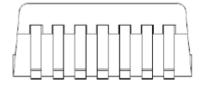


● Package Dimensions

Marking side



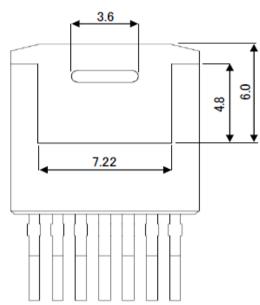




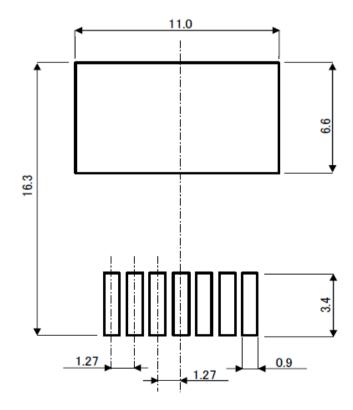
UNIT:mm

Package Dimensions





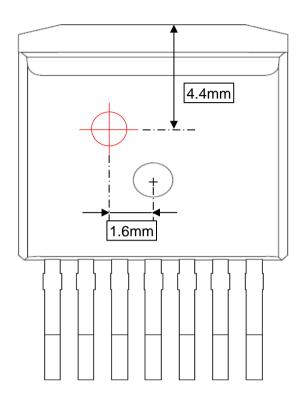
Refference Copper Plate Area Dimension



UNIT:mm

●Die Bonding Layout





- · Front view of the packaging.
- · Dimensions are design values.
- · If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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